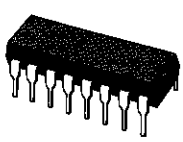
SGS-THOMSON MICROELECTRONICS

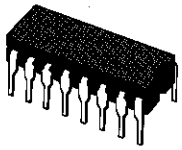
M54/74HC4049
M54/74HC4050

HC4049 HEX BUFFER/CONVERTER (INVERTER)
HC4050 HEX BUFFER/CONVERTER

- HIGH SPEED
  t_{PD} = 9 ns (TYP.) AT V_{CC} = 5 V
- LOW POWER DISSIPATION
  I_{CC} = 1 µA (MAX.) AT T_A = 25 °C
- HIGH NOISE IMMUNITY
  $V_{NIH} = V_{NIL}$ = 28 % V_{CC} (MIN.)
- OUTPUT DRIVE CAPABILITY
  15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE
  $|I_{OH}| = I_{OL}$ = 6 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE
  V_{CC} (OPR) = 2 V TO 6 V
- PIN AND FUNCTION COMPATIBLE
  WITH 4049B/4050B



B1R
(Plastic Package)



F1R
(Ceramic Package)



M1R
(Micro Package)



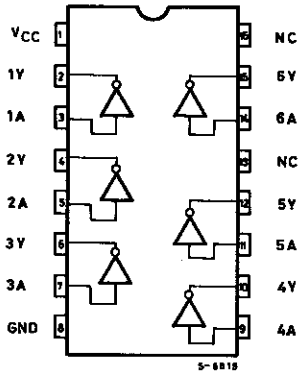
C1R
(Chip Carrier)

ORDER CODES :

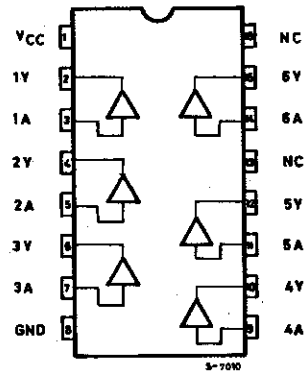
M54HCXXXXF1R M74HCXXXXM1R
M74HCXXXXB1R M74HCXXXXC1R

PIN CONNECTIONS (top view)

HC4049



HC4050



NC =
No Internal
Connection

DESCRIPTION

The M54/74HC4049 and the M54/74HC4050 are high speed CMOS HEX BUFFER fabricated in silicon gate C^2MOS technology.

They have the same high speed performance of LSTTL combined with true CMOS low power consumption.

The M54/75HC4049 is an inverting buffer, while the M54/74HC4050 is a non-inverting buffer.

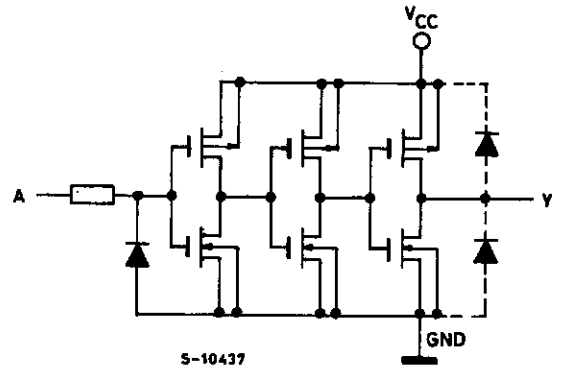
The internal circuit is composed of 3 stage or 2-stage inverters, which provides high noise immunity and a stable output.

Input protection circuits are different from those of the high speed CMOS IC's.

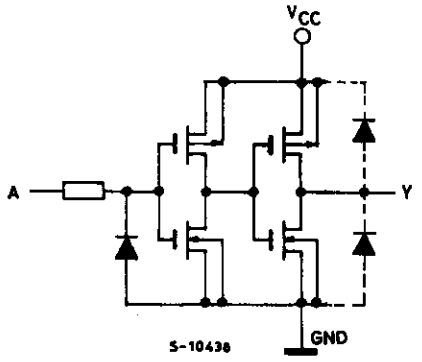
The VCC side diodes are designed to allow logic-level convertion from high-level voltages (up to 15 V) to low-level voltages.

CIRCUIT SCHEMATIC (Per Gate)

HC4049

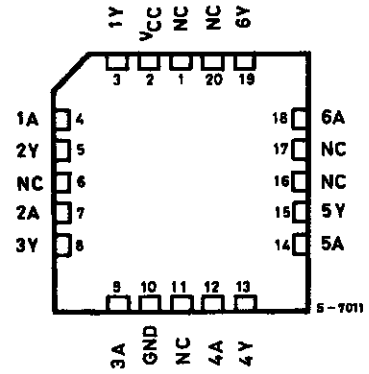


HC4050

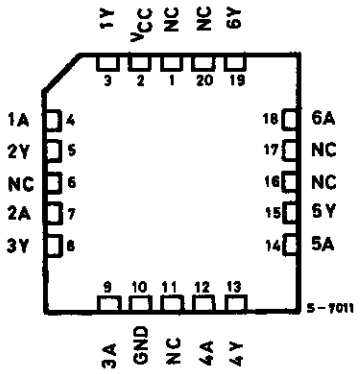


CHIP CARRIER

HC4049



HC4050



NC =No Internal Connection

TRUTH TABLE (HC4049)

INPUT	OUTPUT
nA	$n\overline{Y}$
L	H
H	L

TRUTH TABLE (HC4050)

INPUT	OUTPUT
nA	nY
L	L
H	H

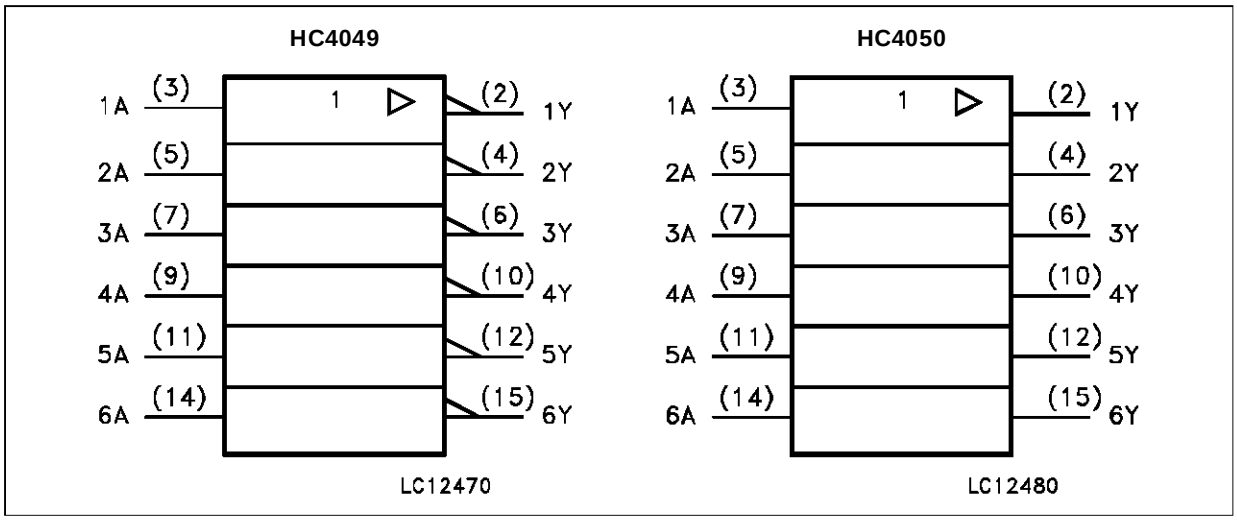
PIN DESCRIPTION (HC4049)

PIN No	SYMBOL	NAME AND FUNCTION
2, 4, 6, 10, 12, 15	$1\overline{Y}$ to $6\overline{Y}$	Data Outputs
3, 5, 7, 9, 11, 14	1A to 6A	Data Inputs
13, 16	NC	Not Connected
8	GND	Ground (0V)
1	V_{CC}	Positive Supply Voltage

PIN DESCRIPTION (HC4050)

PIN No	SYMBOL	NAME AND FUNCTION
2, 4, 6, 10, 12, 15	1Y to 6Y	Data Outputs
3, 5, 7, 9, 11, 14	1A to 6A	Data Inputs
13, 16	NC	Not Connected
8	GND	Ground (0V)
1	V_{CC}	Positive Supply Voltage

IEC LOGIC SYMBOLS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7	V
V_I	DC Input Voltage	-0.5 to V_{CC} + 0.5	V
V_O	DC Output Voltage	-0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	± 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Source Sink Current Per Output Pin	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
P_D	Power Dissipation	500 (*)	mW
T_{stg}	Storage Temperature	-65 to +150	°C
T_L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.
(*) 500 mW: ≅ 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Value	Unit
V_{CC}	Supply Voltage		2 to 6	V
V_I	Input Voltage		0 to V_{CC}	V
V_O	Output Voltage		0 to V_{CC}	V
T_{op}	Operating Temperature: **M54HC** Series **M74HC** Series		-55 to +125 -40 to +85	^oC ^oC
t_r, t_f	Input Rise and Fall Time	V_{CC} = 2 V	0 to 1000	ns
		V_{CC} = 4.5 V	0 to 500	
		V_{CC} = 6 V	0 to 400	

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)			T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
V_{IH}	High Level Input Voltage	2.0			1.5			1.5		1.5		V
		4.5			3.15			3.15		3.15		
		6.0			4.2			4.2		4.2		
V_{IL}	Low Level Input Voltage	2.0					0.5		0.5		0.5	V
		4.5					1.35		1.35		1.35	
		6.0					1.8		1.8		1.8	
V_{OH}	High Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O=-20 µA	1.9	2.0		1.9		1.9		V
		4.5			4.4	4.5		4.4		4.4		
		6.0			5.9	6.0		5.9		5.9		
		4.5		I_O=-6.0 mA	4.18	4.31		4.13		4.10		
		6.0		I_O=-7.8 mA	5.68	5.8		5.63		5.60		
V_{OL}	Low Level Output Voltage	2.0	V_I = V_{IH} or V_{IL}	I_O= 20 µA		0.0	0.1		0.1		0.1	V
		4.5				0.0	0.1		0.1		0.1	
		6.0				0.0	0.1		0.1		0.1	
		4.5		I_O= 6.0 mA		0.17	0.26		0.33		0.40	
		6.0		I_O= 7.8 mA		0.18	0.26		0.33		0.40	
I_I	Input Leakage Current	6.0	V_I = V_{CC} or GND V_I = 15 V				±0.1 ±0.5		±1 ±5		±1	µA
I_{CC}	Quiescent Supply Current	6.0	V_I = V_{CC} or GND				1		10		20	µA

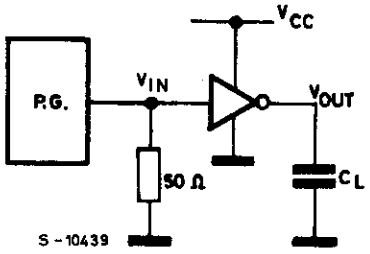
AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns)

Symbol	Parameter	Test Conditions			Value							Unit
		V_{CC} (V)	C_L (pF)		T_A = 25 °C 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
t_{TLH} t_{THL}	Output Transition Time	2.0	50			25	60		75		90	ns
		4.5				7	12		15		18	
		6.0				6	10		13		15	
t_{PLH} t_{PHL}	Propagation Delay Time	2.0	50			30	75		95		115	ns
		4.5				9	15		19		23	
		6.0				8	13		16		20	
		2.0	150			45	100		125		150	ns
		4.5				14	20		25		30	
		6.0				12	17		21		26	
C_{IN}	Input Capacitance					5	10		10		10	pF
C_{PD} (*)	Power Dissipation Capacitance					26						pF

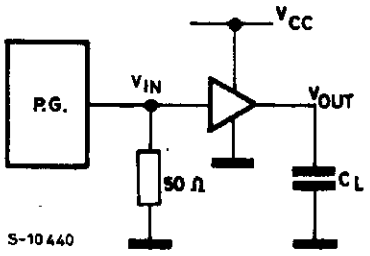
C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}$ (per Gate)

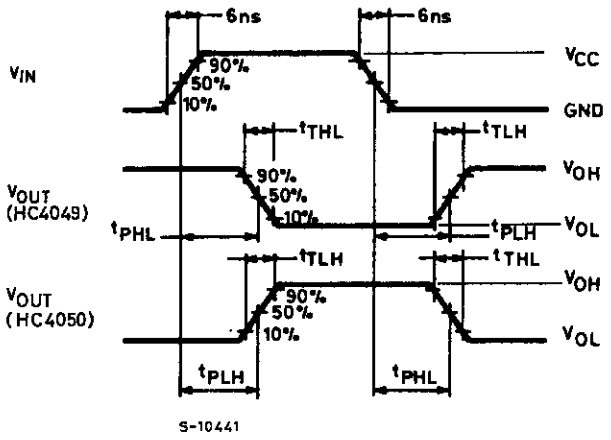
SWITCHING CHARACTERISTICS TEST WAVEFORM

HC4049



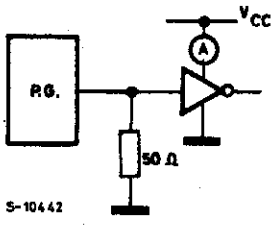
HC4050



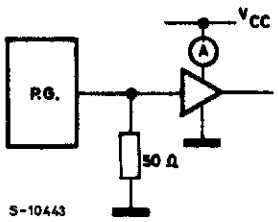


TEST CIRCUIT I_{CC} (Opr.)

HC4049



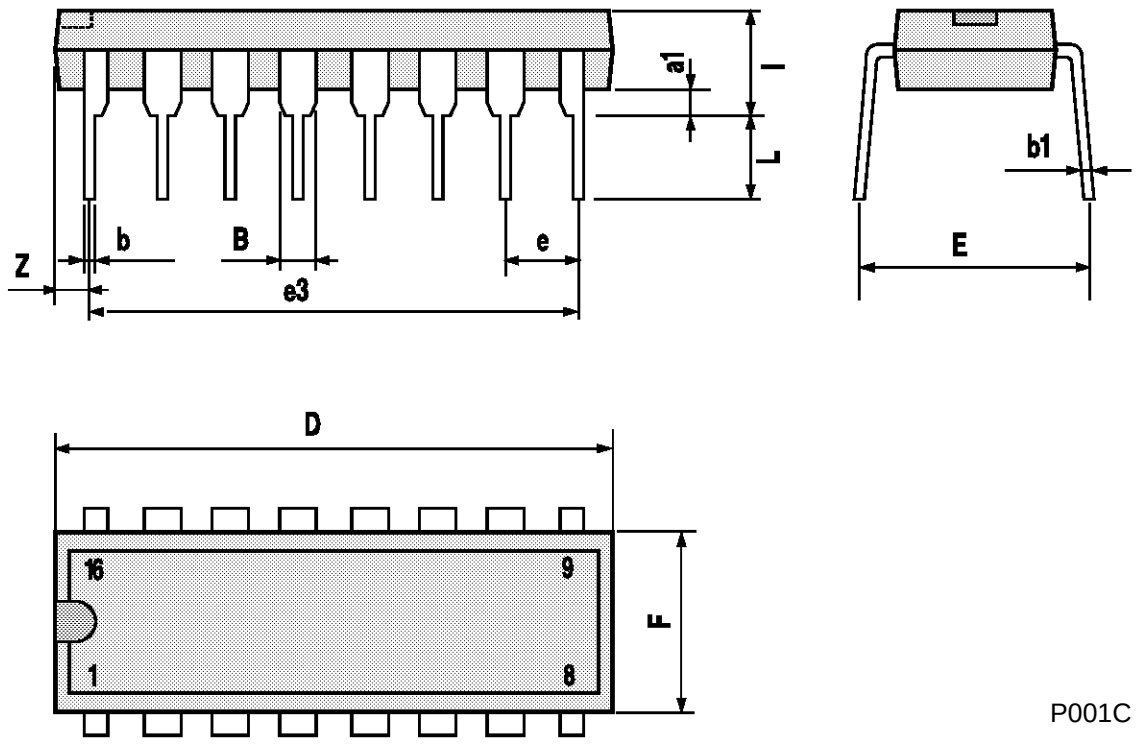
HC4050



INPUT WAVEFORM IS THE SAME AS THAT IN CASE OF SWITCHING CHARACTERISTICS TEST.

Plastic DIP16 (0.25) MECHANICAL DATA

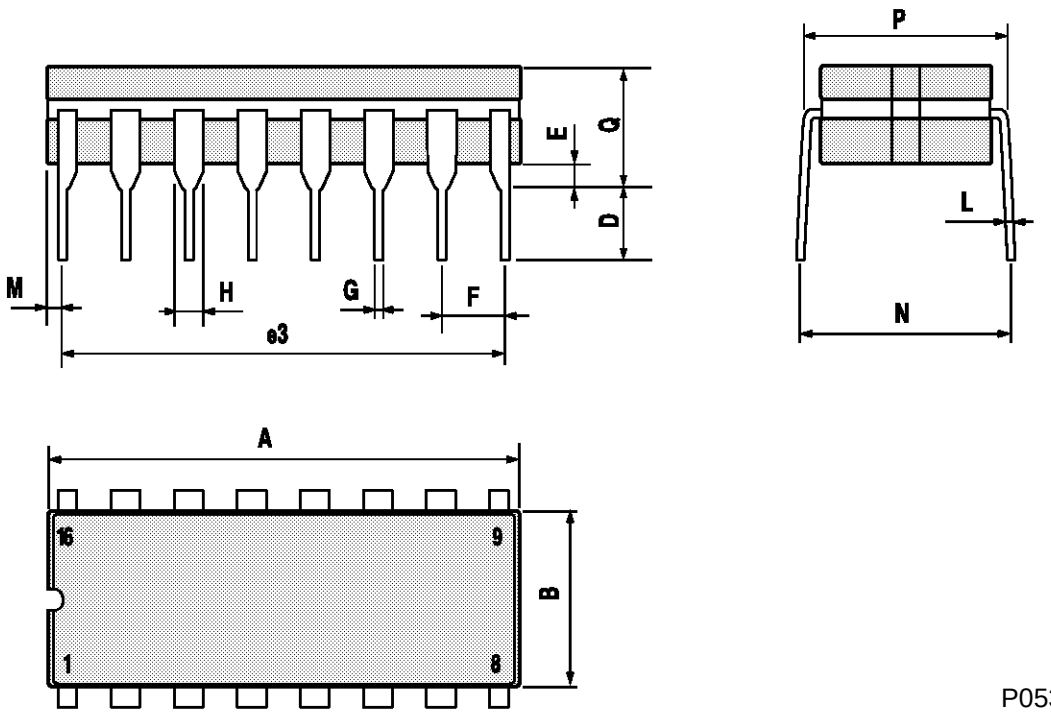
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



P001C

Ceramic DIP16/1 MECHANICAL DATA

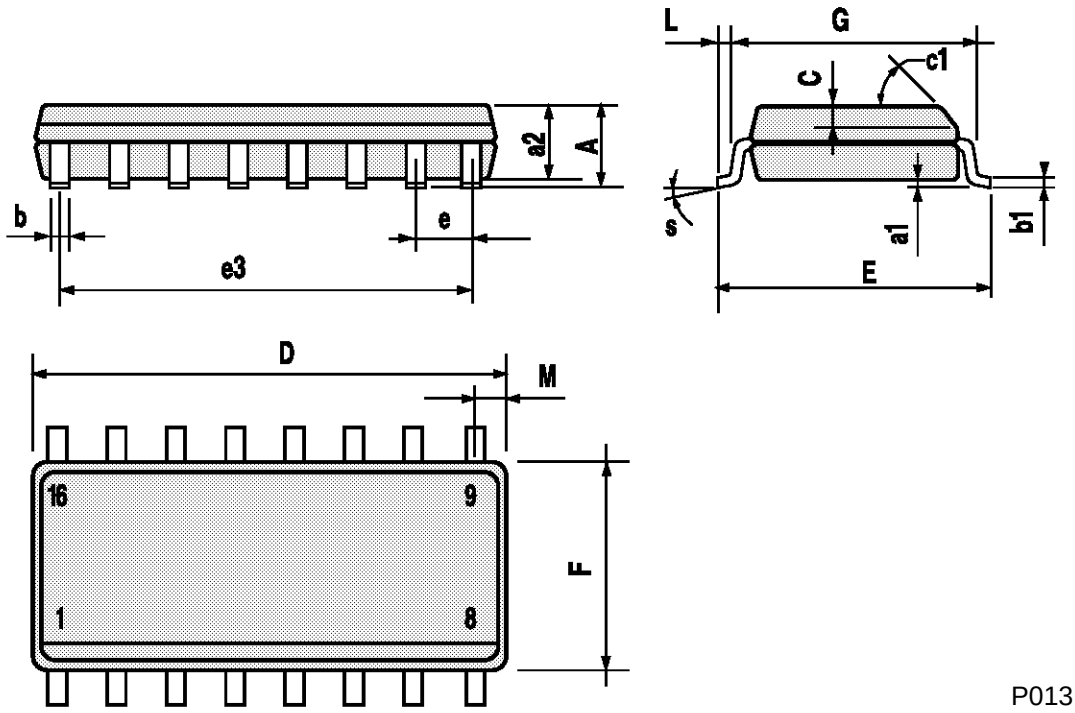
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			20			0.787
B			7			0.276
D		3.3			0.130	
E	0.38			0.015		
e3		17.78			0.700	
F	2.29		2.79	0.090		0.110
G	0.4		0.55	0.016		0.022
H	1.17		1.52	0.046		0.060
L	0.22		0.31	0.009		0.012
M	0.51		1.27	0.020		0.050
N			10.3			0.406
P	7.8		8.05	0.307		0.317
Q			5.08			0.200



P053D

SO16 (Narrow) MECHANICAL DATA

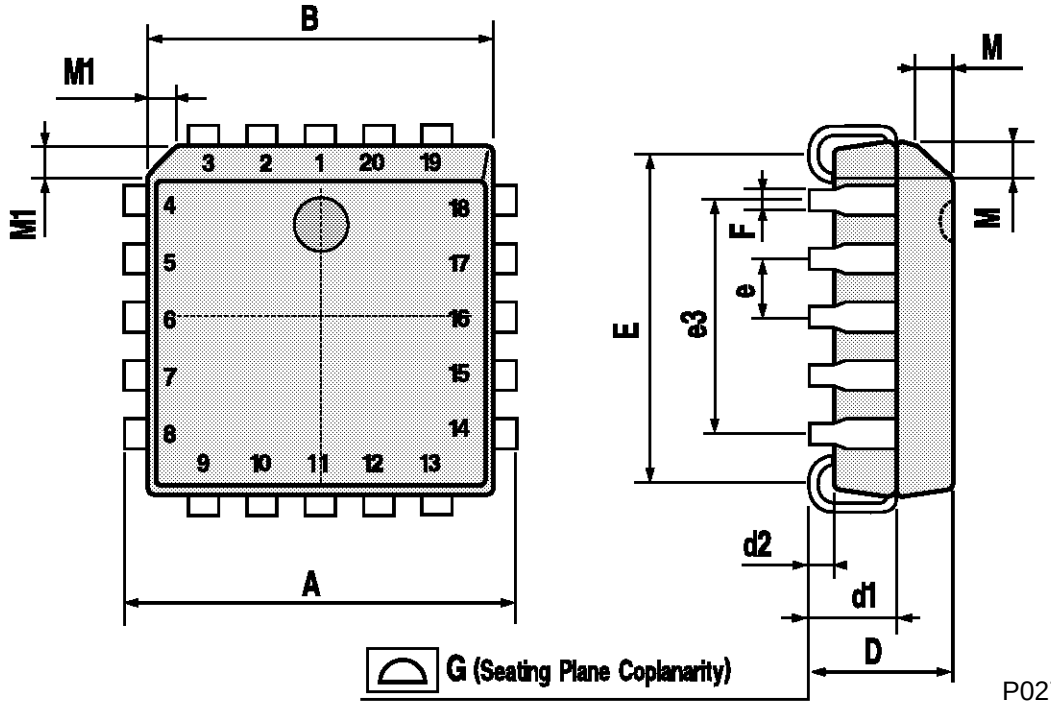
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.004		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



P013H

PLCC20 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	9.78		10.03	0.385		0.395
B	8.89		9.04	0.350		0.356
D	4.2		4.57	0.165		0.180
d1		2.54			0.100	
d2		0.56			0.022	
E	7.37		8.38	0.290		0.330
e		1.27			0.050	
e3		5.08			0.200	
F		0.38			0.015	
G			0.101			0.004
M		1.27			0.050	
M1		1.14			0.045	



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied.
SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1994 SGS-THOMSON Microelectronics - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES
Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A